

NTE5800 thru NTE5809 Axial Lead Standard Recovery Silicon Rectifiers, 3 Amp

Description:

The NTE5800 through NTE5809 silicon rectifiers are designed for use in power supplies and other applications having need of a device with the following features:

- High Current to Small Size
- High Surge Current Capability
- Low Forward Voltage Drop

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}

Working Peak Reverse Voltage, V_{RWM}

DC Blocking Voltage, V_R

NTE5800	50V
NTE5801	100V
NTE5802	200V
NTE5803	300V
NTE5804	400V
NTE5805	500V
NTE5806	600V
NTE5808	800V
NTE5809	1000V

Non-Repetitive Peak Reverse Voltage, V_{RSM}

NTE5800	100V
NTE5801	200V
NTE5802	400V
NTE5803	425V
NTE5804	525V
NTE5805	625V
NTE5806	800V
NTE5808	1000V
NTE5809	1200V

Average Rectified Forward Current, I_O

(Single Phase Resistive Load, 1/2" Leads, $T_L = +105^\circ\text{C}$) 3A

Non-Repetitive Peak Surge Current, I_{FSM}

(Surge Applied at Rated Load Conditions, One Cycle) 200A

Operating Junction Temperature Range, T_J -65° to $+175^\circ\text{C}$

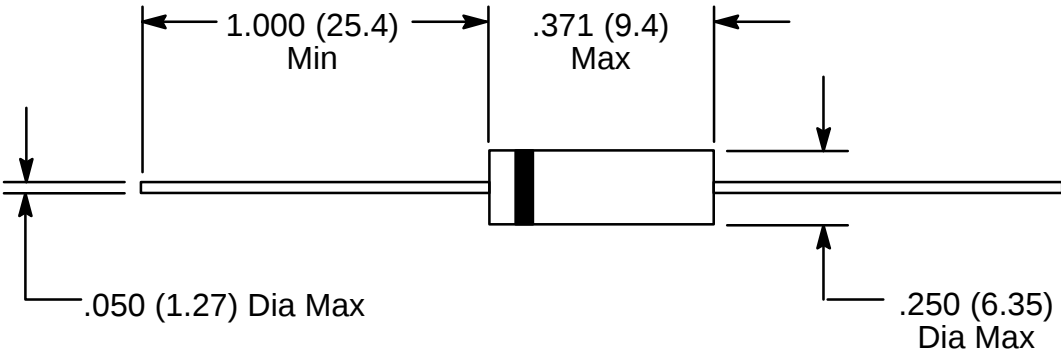
Storage Junction Temperature Range, T_{stg} -65° to $+175^\circ\text{C}$

Thermal Resistance, Junction-to-Ambient (PC Board Mount, 1/2" Leads), R_{thJA} $+53^\circ\text{C/W}$

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	V_F	$i_F = 9.4A$, Note 1	–	–	1.2	V
Average Reverse Current	$I_{R(AV)}$	Note 1	–	–	500	μA
DC Reverse Current	I_R	Rated DC Voltage, $T_L = 150^{\circ}C$	–	–	500	μA

Note 1. Measured in a single–phase half–wave circuit and operated at rated load conditions:
 $T_L = 105^{\circ}C$. $I_O = 3A$. $V_r = V_{RWM}$.



Color Band Denotes Cathode